

### Vishay Semiconductors

# Tandem Insulated SOT-227 Power Module Hyperfast Rectifier, 60 A



SOT-227

PRODUCT SUMMARY					
$V_{R}$	600 V				
I <sub>F(AV)</sub> per module at T <sub>C</sub> = 126 °C	60 A				
t <sub>rr</sub>	39 ns				

#### **FEATURES**

- Two fully independent diodes
- Ceramic fully insulated package (V<sub>ISOL</sub> = 2500 V<sub>AC</sub>)



- Hyperfast reverse recovery
- Optimized for power conversion: welding and industrial SMPS applications
- Industry standard outline
- Plug-in compatible with other SOT-227 packages
- · Easy to assemble
- · Direct mounting to heatsink
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

#### **DESCRIPTION**

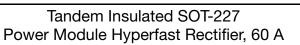
The UFH60GA60P insulated modules integrate two state of the art Vishay hyperfast recovery rectifiers in the compact, industry standard SOT-227 package. The planar structure of the diodes, and the platinum doping life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness, and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be a predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, and dc-to-dc converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	$V_R$		600	V	
Continuous forward current per diode	l <sub>F</sub>	T <sub>C</sub> = 85 °C	56	Α	
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	200		
Maximum power dissipation per module	$P_D$	T <sub>C</sub> = 85 °C	230	W	
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 min	2500	V	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 175	°C	

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA		600	-	-	
Familia de la casa de	V <sub>FM</sub>	I <sub>F</sub> = 30 A		-	2.08	3.8	
		I <sub>F</sub> = 60 A		-	2.36	4.78	V
Forward voltage		I <sub>F</sub> = 30 A	- T <sub>J</sub> = 125 °C	-	1.79	1.92	
		I <sub>F</sub> = 60 A		-	2.1	2.42	
Reverse leakage current I <sub>RM</sub>	$V_R = V_R$ rated		-	0.03	75	μA	
	IRM	$T_J = 175  ^{\circ}\text{C},  V_R = V_R  \text{rated}$		-	0.1	1.0	mA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V		-	33	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Davida de la compansión	+	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	39	80	- ns
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	66	110	
Parl and a second	1	T <sub>J</sub> = 25 °C		-	3	7	A
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	7	11	
Reverse recovery charge Q <sub>rr</sub>		T <sub>J</sub> = 25 °C		-	58	280	nC
	T <sub>J</sub> = 125 °C		1	235	605	11C	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	- R <sub>thJC</sub>		-	-	0.78	
Junction to case, both leg conducting			-	-	0.39	°C/W
Case to heatsink per module	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	1.3	-	N⋅m



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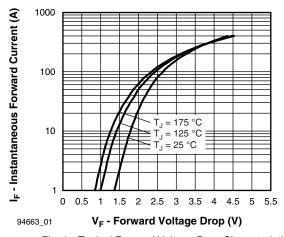


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Diode)

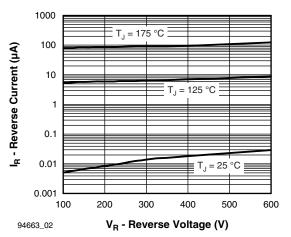


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

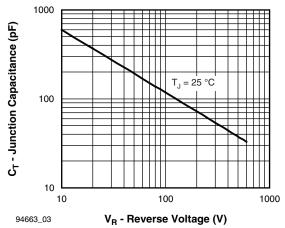


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

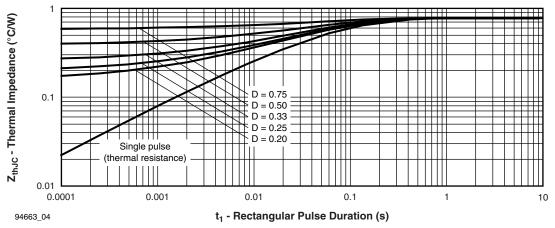


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Diode)

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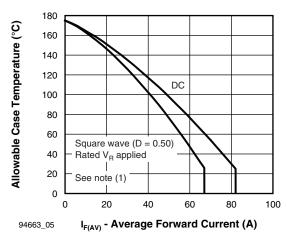


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

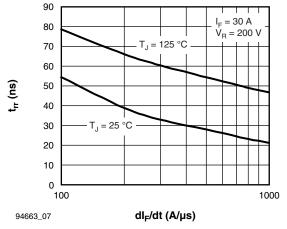


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

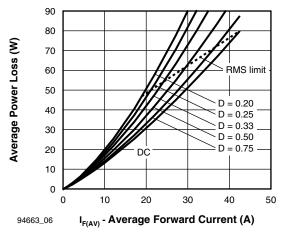


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

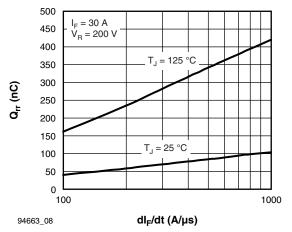


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

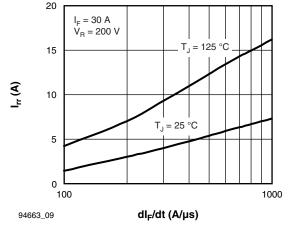


Fig. 9 - Typical Stored Current vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6);} \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = 80 \text{ \% rated } V_R \text{ (1 - D); } I_R \text{ (2 - D);$ 



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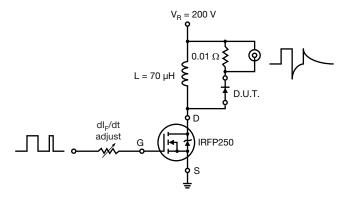
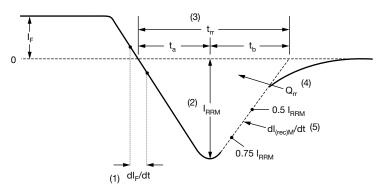


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_{r}$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 11 - Reverse Recovery Waveform and Definitions

## UFH60GA60P

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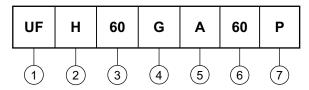


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### **ORDERING INFORMATION TABLE**

Device code



1 - Ultrafast rectifier

2 - Hyperfast rectifier

- Current rating (60 = 60 A)

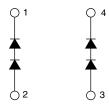
4 - Circuit configuration (2 separate diodes, tandem configuration)

- Package indicator (SOT-227 standard isolated base)

6 - Voltage rating (60 = 600 V)

7 - P = Lead (Pb)-free

### **CIRCUIT CONFIGURATION**



LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95036</u>					
Packaging information	www.vishay.com/doc?95037				





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